	TET ESTEL AS ESTONIA	**December 2015**

Series
D343-1000

Rectifier Press-Pack Diode Type D343-1000

Designed for rectifiers and industrial applications

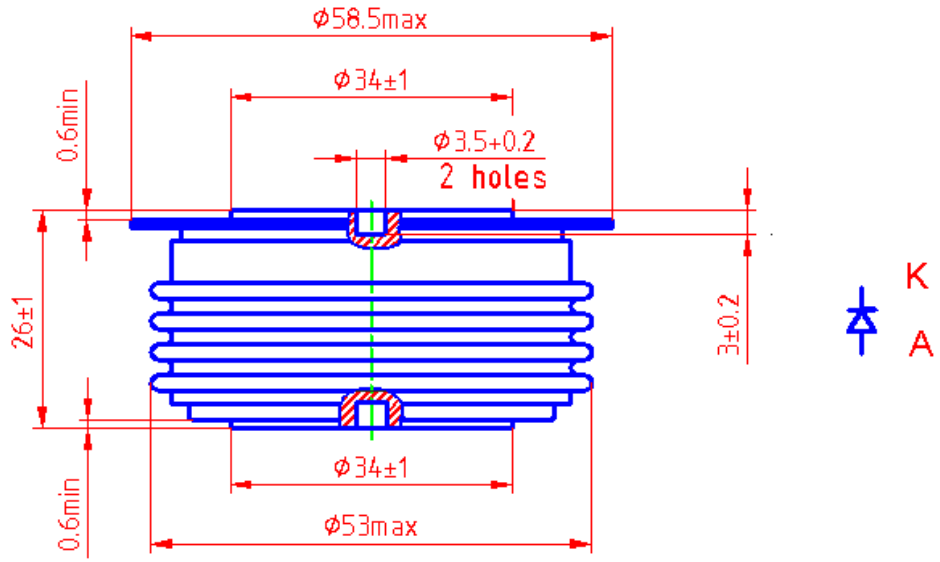
Maximum mean forward current				I_{FAV}	**1000 A**	
Maximum repetitive peak reverse voltage				U_{RRM}	**2600 ÷3600 V**	
Reverse recovery time				**trr** (typ)	**40 µs**	
U_{RRM}, V	2600	2800	3000	3200	3400	3600
Voltage code	26	28	30	32	34	36
Tvj, °C	- 60 ÷ 150					

MAXIMUM ALLOWABLE RATINGS					
Symbols and parameters		Units	D343-1000	Conditions	
I_{FAV}	Mean forward current	A	1000 1505	Tc=100 °C, Tc=55 °C, 180° half-sine wave, 50 Hz	
I_{FRMS}	RMS forward current	A	1570	Tc=100 °C	
I_{FSM}	Surge forward current	kA	15 17	Tvj=150°C Tvj=25°C	tp=10 ms U_R=0
I^2t	Limiting load integral	kA^2s	1125 1445	Tvj=150°C Tvj=25°C	
U_{RRM}	Repetitive peak reverse voltage	V	2600÷3600	Tj min≤Tvj≤Tjм 180° half-sine wave, 50 Hz	
U_{RSM}	Non-repetitive peak reverse voltage	V	2700÷3700	Tj min≤Tvj≤Tjм 180° half-sine wave tp=10 ms, Single pulse	
Tstg	Storage temperature	°C	-60÷80		
Tvj	Junction temperature	°C	-60÷150		
CHARACTERISTICS					
U_{FM}	Peak forward voltage	V	1,9	Tvj=25°C, I_{TM}=3,14 I_{TAV}	
$U_{F(TO)}$	Threshold voltage	V	0,8	Tvj=150°C 1,57 I_{TAV}< I_T <4,71 I_{TAV}	
R_T	Forward slope resistance	mΩ	0,35		
I_{RRM}	Repetitive peak reverse current	mA	50	Tvj=150°C, U_R= U_{RRM}	

CHARACTERISTICS				
Symbols and parameters		Units	D343-1000	Conditions
Qrr	Recovered charge (typ)	μC	3000	Tvj=150°C I_F=1000 A di_R/dt =10 A/μs U_R=100V
trr	Reverse recovery time (typ)	μs	40	
Irrм	Peak reverse recovery current (typ)	A	150	
Rthjc	Thermal resistance junction to case	°C/W	0,03	Direct current, double side cooled

ORDERING					
	D	**343**	**1000**	**30**	
	1	**2**	**3**	**4**	

1. Diode
2. Design version
3. Mean forward current, A
4. Voltage code (30=3000 V)



Mounting force : 13 ÷ 19 kN
Weight : 320 grams